

December 2013

FDPF390N15A

N-Channel PowerTrench® MOSFET

150 V, 15 A, 40 mΩ

Features

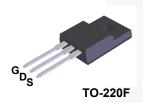
- $R_{DS(on)}$ = 31 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 15 A
- · Fast Switching Speed
- Low Gate Charge, Q_G = 14.3 nC (Typ.)
- High Performance Trench Technology for Extremely Low $R_{\mbox{\footnotesize{DS(on)}}}$
- · High Power and Current Handling Capability
- · RoHS Compliant

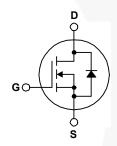
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintain-ing superior switching performance.

Applications

- · Consumer Appliances
- LED TV
- · Synchronous Rectification
- Uninterruptible Power Supply
- · Motor Solar Inverter





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FDPF390N15A	Unit	
V _{DSS}	Drain to Source Voltage	Drain to Source Voltage			V	
V _{GSS}	Gate to Source Voltage			±20	V	
	Drain Current	- Continuous (T _C = 25°C,Silicon Limited	d)	15	А	
^I D	Dialii Current	- Continuous (T _C = 100°C,Silicon Limite	ed)	10	1 ^	
I _{DM}	Drain Current	- Pulsed (Note 1)		60	Α	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		ote 2)	78	mJ	
dv/dt	Peak Diode Recovery dv/dt	Peak Diode Recovery dv/dt (Note 3)		6.0	V/ns	
D	Dower Discipation	$(T_C = 25^{\circ}C)$		22	W	
P_{D}	Power Dissipation	- Derate above 25°C		0.18	W/°C	
T_J , T_{STG}	Operating and Storage Temperature Range			-55 to +175	οС	
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.			300	°C	

Thermal Characteristics

Symbol	Parameter	FDPF390N15A	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	5.7	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.		- 0/00

Package Marking and Ordering Information

	Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
F	FDPF390N15A	FDPF390N15A	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25$ °C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	150	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu A$, Referenced to $25^{\circ}C$	-	0.1	-	V/ºC
I _{DSS} Zero Gate Voltage Drain Current	Zero Gate Voltage Drain Current	V _{DS} = 120 V, V _{GS} = 0 V	-	-	1	μА
	3	$V_{DS} = 120 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	500	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	2.0	-	4.0	٧
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 15 \text{A}$	-	31	40	mΩ
9FS	Forward Transconductance	V _{DS} = 10 V, I _D = 15 A	-	32	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 75 V V 0 V	-	965	1285	pF
C _{oss}	Output Capacitance	$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}$ f = 1 MHz		96	130	pF
C _{rss}	Reverse Transfer Capacitance			5.8	-	pF
C _{oss(er)}	Energy Related Output Capacitance	V _{DS} = 75 V,V _{GS} = 0 V		169	-	pF
Q _{g(tot)}	Total Gate Charge at 10V		-	14.3	18.6	nC
Q _{gs}	Gate to Source Gate Charge	$V_{DS} = 75 \text{ V}, I_{D} = 27 \text{ A}$		5.0	-	nC
Q _{gs2}	Gate Charge Threshold to Plateau	V _{GS} = 10 V	-	2.0	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note 4)	-	3.5	-	nC
ESR	Equivalent Series Resistance (G-S)	f = 1 MHz	-	1.4	-	Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	14	38	ns
t _r		$V_{DD} = 75 \text{ V}, I_D = 27 \text{ A}$	-	10	30	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_G = 4.7 \Omega$	/ -	20	50	ns
t _f	Turn-Off Fall Time	(Note 4)	-	5	20	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode	Maximum Continuous Drain to Source Diode Forward Current			15	Α
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current			-	64	Α
V_{SD}	Drain to Source Diode Forward Voltage V _{GS} = 0 V, I _{SD} = 15 A		-	-	1.25	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 27 A		63	-	ns
Q _{rr}	Reverse Recovery Charge	Recovery Time $V_{GS} = 0 \text{ V, } I_{SD} = 27 \text{ A}$ Recovery Charge $dI_F/dt = 100 \text{ A}/\mu\text{s}$		131	_	nC

- **Notes:**1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. Starting $T_J = 25$ °C, L = 3 mH, $I_{SD} = 7.2$ A
- 3. $I_{SD} \le 15$ A, di/dt ≤ 200 A/ μ s, $V_{DD} \le BV_{DSS}$, starting $T_J = 25^{\circ}C$
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

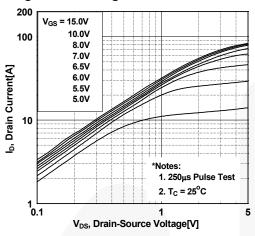


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

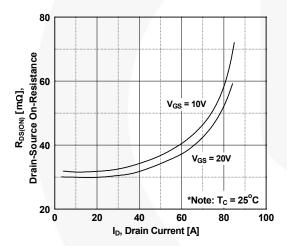


Figure 5. Capacitance Characteristics

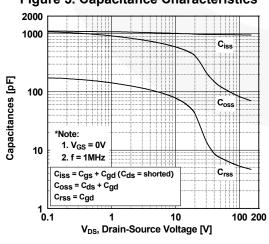


Figure 2. Transfer Characteristics

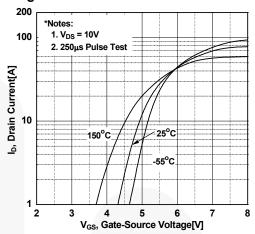


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

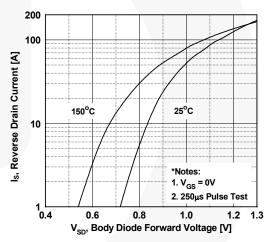
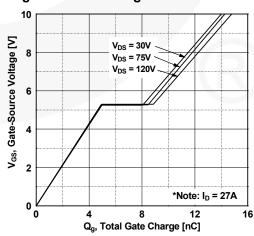


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

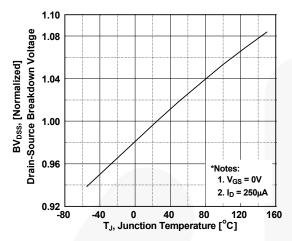


Figure 9. Maximum Safe Operating Area

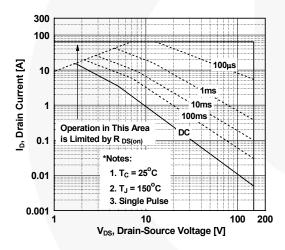


Figure 11. Eoss vs. Drain to Source Volatage

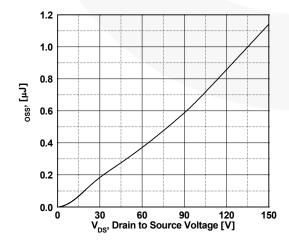


Figure 8. On-Resistance Variation vs. Temperature

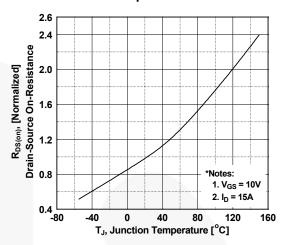


Figure 10. Maximum Drain Current vs. Case Temperature

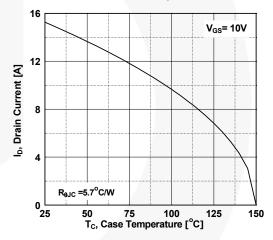
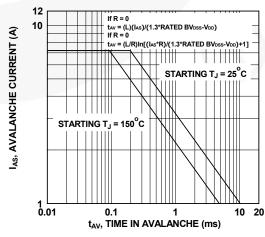
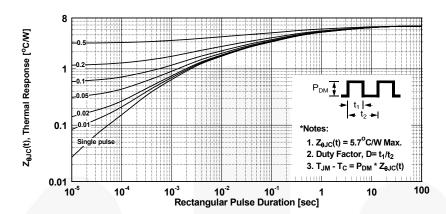


Figure 12. Unclamped Inductive Switching Capability



Typical Performance Characteristics (Continued)

Figure 13. Transient Thermal Response Curve



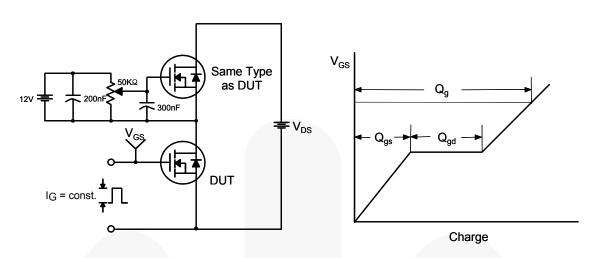


Figure 14. Gate Charge Test Circuit & Waveform

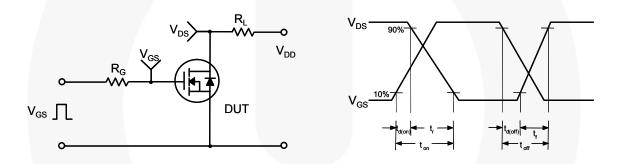


Figure 15. Resistive Switching Test Circuit & Waveforms

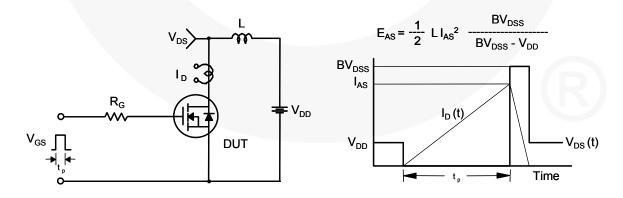


Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms

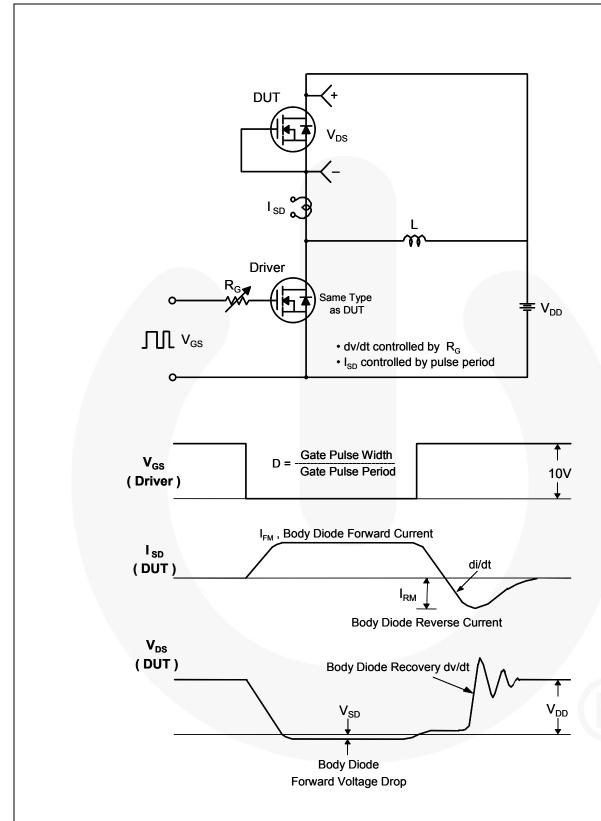
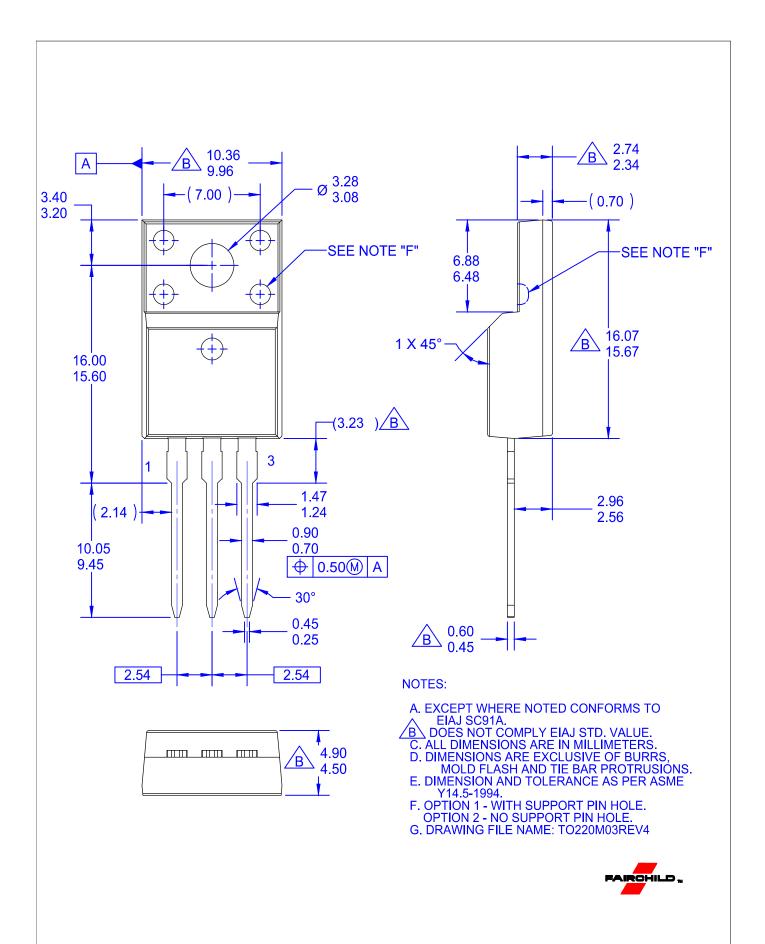


Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms







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Datasheet Identification	Product Status	Definition				
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.				
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